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(54) ELECTRODE MATERIAL OF GALLIUM NITRIDE COMPOUND SEMICONDUCTOR

(57)Abstract:

PURPOSE: To materialize a light emitting device, wherein driving voltage is lowered and brightness is raised, making use of a gallium nitride compound semiconductor, by getting the ohmic contact from a p-type layer and an n-type layer.

CONSTITUTION: At least one kind of metal being selected from the group consisting of Au, Pt, Ag, and Ni or their alloy is used for  $\text{GaXAl}_{1-X}\text{N}$  (but,  $0 \leq X \leq 1$ ) doped with p-type impurities, and at least one kind of metal being selected from the group consisting of Al, Cr, Ti, and In or their alloy is used for  $\text{GaXAl}_{1-X}\text{N}$  doped with n-type impurities.

